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(54) **SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

A novel semiconductor device is provided. The semiconductor device includes a first layer; a second layer over the first layer; and a third layer over the second layer. The first layer includes a functional circuit including a first transistor, the second layer includes a plurality of pixel circuits each including a second transistor, the third layer includes a plurality of light-emitting elements, one of the plurality of pixel circuits is electrically connected to one of the plurality of light-emitting elements, the functional circuit has a function of controlling an operation of the pixel circuit, and the pixel circuit has a function of controlling emission luminance of the light-emitting element.